

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2316	(438/149,151).CCLS	US-PGPUB; USPAT; IBM_TDB	OR	OFF	2005/08/29 09:16
S2	20	chen-kun-hong.in.	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:16
S3	38248	TFT "thin film transistor"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:46
S4	19	S2 and S3	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:18
S5	3958	photoresist same residue	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:48
S6	34143	buffer with layer	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:28
S7	13759	idd	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:18
S8	84090	ito	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:18
S9	226	S3 and S5	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:18
S10	19	S9 and S6	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:19
S11	1840	S1 and @ad<"20030630"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:27
S12	14	S10 and @ad<"20030630"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:48
S13	8	S9 and S7	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:26
S14	7	S13 and @ad<"20030630"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 09:26
S15	41067	TFT "thin film transistor"	EPO; JPO; DERWENT	OR	ON	2005/08/29 09:28
S16	1133	photoresist same residue	EPO; JPO; DERWENT	OR	ON	2005/08/29 09:28

S17	21317	buffer with layer	EPO; JPO; DERWENT	OR	ON	2005/08/29 09:28
S18	2	S15 and S16 and S17	EPO; JPO; DERWENT	OR	ON	2005/08/29 09:29
S19	2358	S3 and S6	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 10:30
S20	396	S19 and ldd and ito	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 10:30
S21	388	S20 and (oxide nitride)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 10:30
S22	304	S21 and @ad<"20030630"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 10:32
S23	232	S22 and ("438"/\$3 "257"/\$3).cccls.	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:55
S24	38248	TFT "thin film transistor"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:46
S25	71140	gate with oxide	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:55
S26	27739	S25 same (etched etching etch etches)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:55
S27	2971	S24 and S26	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:46
S28	3958	photoresist same residue	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:48
S29	65	S27 and S28	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:48
S30	52	S29 and @ad<"20030630"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:55
S31	40766	gate adj oxide	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:55
S32	8945	S31 with (etched etching etch etches)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:55

S33	498	S24 and S32	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:55
S34	440	S33 and @ad<"20030630"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 13:29
S35	395	S34 and ("438"/\$3 "257"/\$3).ccls.	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 12:56
S36	8	("20010031519" "20020004260" "5328861" "5365080" "5904508" "6287898").PN. OR ("6534350").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/29 13:29
S37	8	S36 and @ad<"20030630"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 13:29
S38	1	("6703267").PN.	US-PGPUB; USPAT; IBM_TDB	OR	OFF	2005/08/29 14:49
S39	1	("6287898").PN.	US-PGPUB; USPAT; IBM_TDB	OR	OFF	2005/08/29 14:49
S40	15	((("20030027412") or ("20030085404") or ("20030116805") or ("20030151095") or ("20040087125") or ("20040126914") or ("5851918") or ("6287898") or ("6403409") or ("6528820") or ("6534350") or ("6537843") or ("6593161") or ("6703266") or ("6703267"))).PN.	US-PGPUB; USPAT; IBM_TDB	OR	OFF	2005/08/29 14:50
S41	234034	chromium "Cr"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 14:51
S42	333441	molybdenum "Mo"	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 14:51
S43	1	thallium/aluminum/thallium TI/Al/TI	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 14:51
S44	50545	(S41 S42) with gate	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 14:51
S45	12	S40 and S44	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 14:56
S46	10	S40 and ldd	US-PGPUB; USPAT; IBM_TDB	OR	ON	2005/08/29 14:56